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		<input checked="" type="checkbox"/> Details <input checked="" type="checkbox"/> Highlight all hit terms locally	
((((((capacitor with ((sidewall spacer) or spacer)) not (((metal adj insulator adj metal) or (metal-insulator-metal) or "MIM")) and (capacitor and ((lower adj electrode) or (bottom adj electrode)) and (sidewall adj spacer)))) and channel) and ((titanium adj nitride) or ("TiN")))) and (("Ta.sub.2 O.sub.5" or (tantalum adj pentoxide)))) and (plasma)) and (ammonia)			

	U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C	3	4
1					US 20020163025	20021107	25	Mixed metal nitride and boride barrier layers	257/295			Vaartstra, Brian A. et al.				
2					US 20020079523	20020627	25	Reduction of damage in semiconductor container	257/296			Zheng, Lingyi A. et al.				
3					US 6538274 B2	20030325	19	Reduction of damage in semiconductor container	257/296	257/303; 257/306		Zheng, Lingyi A. et al.				
4					US 6445023 B1	20020993	23	Mixed metal nitride and boride barrier layers	257/295	257/306; 257/308;		Vaartstra, Brian A. et al.				
5					US 6432835 B1	20020813	59	Process for fabricating an integrated circuit	438/720	257/E21.01 1;		Yunogami, Takashi et al.				
6					US 6399399 B2	20020604	26	Method for manufacturing	438/3	438/240; 438/253		Yamamoto, Tomoe				
7					US 6218693 B1	20010417	12	Dynamic random access memory (DRAM) cell	257/296	257/300; 257/301;		Lu, Chih-Yuan				
8					US 6149179 A	20001031	13	Method of forming a crown capacitor for a	438/254	257/E21.01 2;		Chen, Yinan et al.				
9					US 6136643 A	20001024	17	Method for fabricating capacitor-over-bit-line	438/253	257/E21.01 9;		Jeng, Erik S. et al.				
10					US 6910931 A	200009104	13	Planarization technique for DRAM cell capacitor	438/240	257/E21.64 8;		Sun, Shih-Wei et al.				
11					US 6003514	19991228	16	Double crown shape	257/303	257/306.		Wu, Shue-Jen				